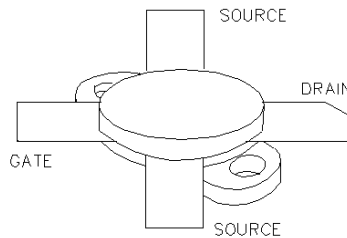




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features low feedback and output capacitances resulting in high F_t transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER VDMOS TRANSISTOR

80.0 Watts Single Ended

Package Style AM

HIGH EFFICIENCY, LINEAR
HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS ($T = 25^{\circ}\text{C}$)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
150 Watts	1.00 $^{\circ}\text{C/W}$	200 $^{\circ}\text{C}$	-65 $^{\circ}\text{C}$ to 150 $^{\circ}\text{C}$	9.0 A	70V	70V	20 V

RF CHARACTERISTICS (80.0 WATTS OUTPUT)

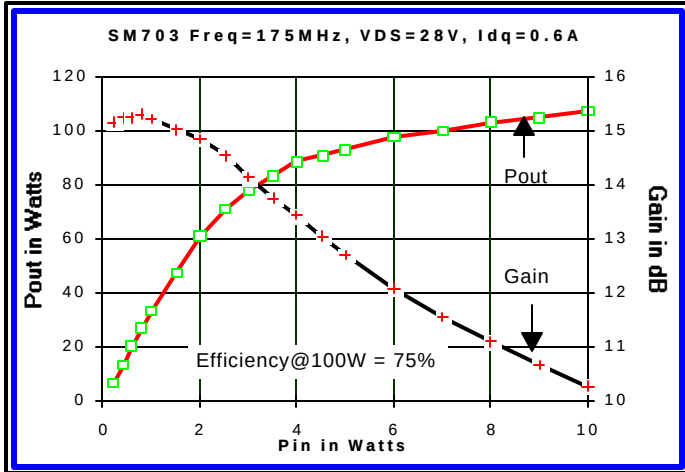
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	13			dB	$I_{dq} = 0.60 \text{ A}$, $V_{ds} = 28.0 \text{ V}$, $F = 175 \text{ MHz}$
η	Drain Efficiency		75		%	$I_{dq} = 0.60 \text{ A}$, $V_{ds} = 28.0 \text{ V}$, $F = 175 \text{ MHz}$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 0.60 \text{ A}$, $V_{ds} = 28.0 \text{ V}$, $F = 175 \text{ MHz}$

ELECTRICAL CHARACTERISTICS (EACH SIDE)

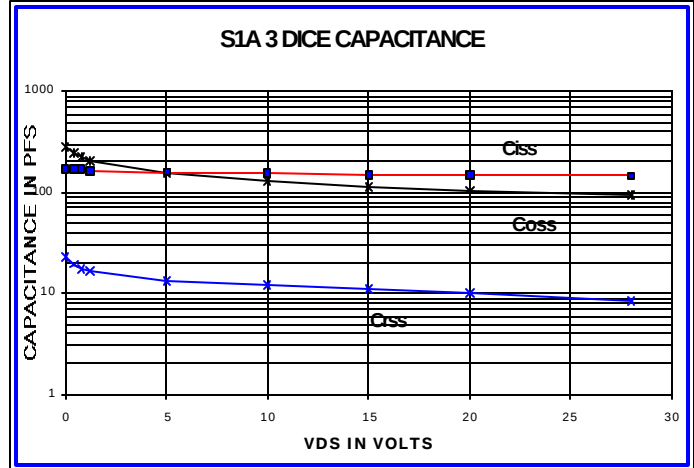
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	$I_{ds} = 60.00 \text{ mA}$, $V_{gs} = 0\text{V}$
Idss	Zero Bias Drain Current			3.0	mA	$V_{ds} = 28.0 \text{ V}$, $V_{gs} = 0\text{V}$
Igss	Gate Leakage Current			1	μA	$V_{ds} = 0\text{V}$ $V_{gs} = 30\text{V}$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.30 \text{ A}$, $V_{gs} = V_{ds}$
gM	Forward Transconductance		3.6		Mho	$V_{ds} = 10\text{V}$, $V_{gs} = 5\text{V}$
Rdson	Saturation Resistance		0.35		Ohm	$V_{gs} = 20\text{V}$, $I_{ds} = 7.50 \text{ A}$
Idsat	Saturation Current		21.00		Amp	$V_{gs} = 20\text{V}$, $V_{ds} = 10\text{V}$
Ciss	Common Source Input Capacitance		150.0		pF	$V_{ds} = 28.0 \text{ V}$, $V_{gs} = 0\text{V}$, $F = 1 \text{ MHz}$
Crss	Common Source Feedback Capacitance		9.0		pF	$V_{ds} = 28.0 \text{ V}$, $V_{gs} = 0\text{V}$, $F = 1 \text{ MHz}$
Coss	Common Source Output Capacitance		96.0		pF	$V_{ds} = 28.0 \text{ V}$, $V_{gs} = 0\text{V}$, $F = 1 \text{ MHz}$

SM703

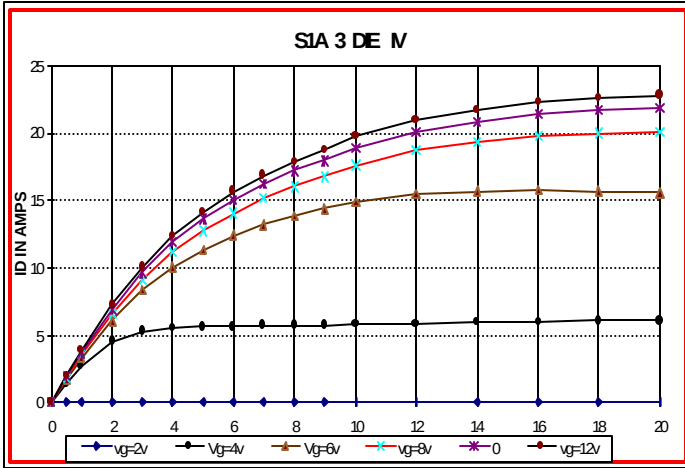
POUT VS PIN GRAPH



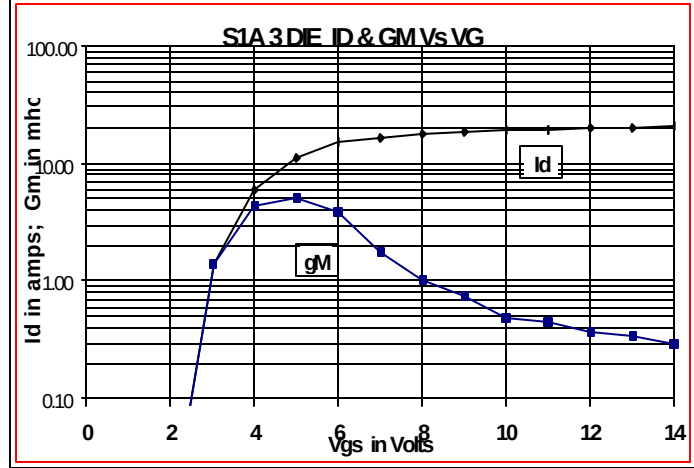
CAPACITANCE VS VOLTAGE



IV CURVE

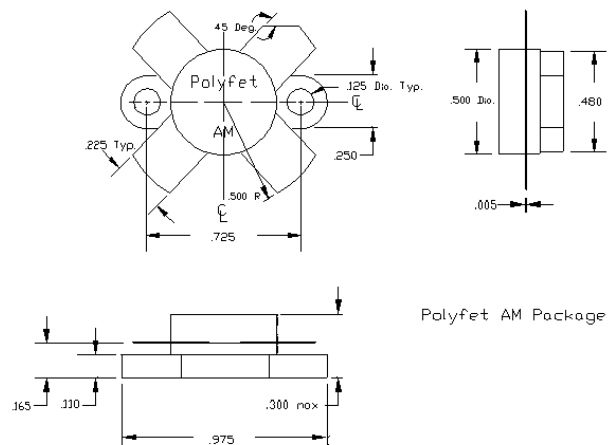
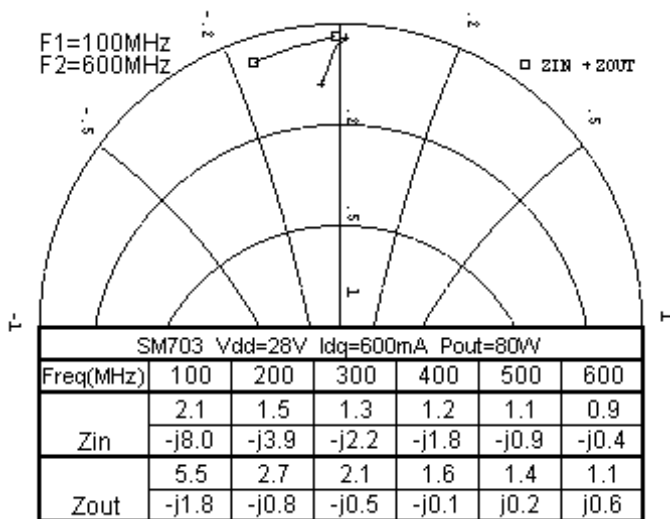


ID & GM VS VGS



Zin Zout

PACKAGE DIMENSIONS IN INCHES



Tolerance .XX +/-0.01 .XXX +/-0.005 inches

POLYFET RF DEVICES

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